



# A1A:450.XX

## VOLTAGE RATINGS

Part Number	$V_{RRM}, V_R$ (V)		$V_{RSM}, V_R$ (V) Max. non-rep. peak reverse voltage
	Max. rep. peak reverse voltage	$T_J = 0$ to $200^\circ\text{C}$	
A1A:450.02	200	200	300
A1A:450.04	400	400	500
A1A:450.06	600	600	700
A1A:450.08	800	800	900

This datasheet applies to:

**Metric thread: A1A:450.XX,  
A1B:450.XX**

**Inch thread: A2A:450.XX,  
A2B:450.XX**

## MAXIMUM ALLOWABLE RATINGS

PARAMETER	VALUE	UNITS	NOTES
$T_J$ Junction Temperature	-40 to 200	$^\circ\text{C}$	-
$T_{stg}$ Storage Temperature	-40 to 200	$^\circ\text{C}$	-
$I_{F(AV)}$	Max. Av. current	A	180° half sine wave
	@ Max. $T_C$	$^\circ\text{C}$	
$I_{F(RMS)}$ Nom. RMS current	940	A	-
$I_{FSM}$ Max. Peak non-rep. surge current	10900	A	50 Hz half cycle sine wave Initial $T_J = 200^\circ\text{C}$ , rated $V_{RRM}$ applied after surge.
	11450		60 Hz half cycle sine wave
	13000		50 Hz half cycle sine wave Initial $T_J = 200^\circ\text{C}$ , no voltage applied after surge.
	13600		60 Hz half cycle sine wave
$I^2t$ Max. $I^2t$ capability	546	kA <sup>2</sup> s	$t = 10\text{ms}$ Initial $T_J = 200^\circ\text{C}$ , rated $V_{RRM}$ applied after surge.
	598		$t = 8.3 \text{ ms}$
	772		$t = 10\text{ms}$ Initial $T_J = 200^\circ\text{C}$ , no voltage applied after surge.
	845		$t = 8.3 \text{ ms}$
$I^{2\frac{1}{2}}$ Max. $I^{2\frac{1}{2}}$ capability	8450	kA <sup>2</sup> s <sup>1/2</sup>	Initial $T_J = 200^\circ\text{C}$ , no voltage applied after surge. for time $t_x = I^{2\frac{1}{2}} * t_x^{1/2}$ . ( $0.1 < t_x < 10\text{ms}$ ). $\frac{I^2t}{t}$
F Mounting Force	30(267)	N.m(Lbf.in)	-



## A1A:450.XX

### CHARACTERISTICS

PARAMETER	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
$V_{FM}$ Peak forward voltage	---	---	1.31	V	Initial $T_J = 25^\circ\text{C}$ , 50-60Hz half sine, $I_{peak} = 1414\text{A}$ .
$V_{F(TO)1}$ Low-level threshold	---	---	0.78	V	$T_J = 200^\circ\text{C}$
$V_{F(TO)2}$ High-level threshold	---	---	0.87		$\text{Av. power} = V_{F(TO)} * I_{F(AV)} + r_F * [I_{F(RMS)}]^2$
$r_{F1}$ Low-level resistance	---	---	0.35	m	Use low values for $I_{FM} < I_{F(AV)}$
$r_{F2}$ High-level resistance	---	---	0.31		
$I_{RM}$ Peak reverse current	---	---	40	mA	$T_J = 200^\circ\text{C}$ . Max. rated $V_{RRM}$
$R_{thJC}$ Thermal resistance, junction-to-case	---	---	0.11	°C/W	DC operation
	---	---	0.12	°C/W	180° sine wave
	---	---	0.13	°C/W	120° rectangular wave
$R_{thCS}$ Thermal resistance, case-to-sink	---	---	0.03	°C/W	Mtg. Surface smooth, flat and greased. Single side.
wt Weight	---	250(8.75)	---	g(oz.)	---
Case Style	DO-205AB(DO-9)				---

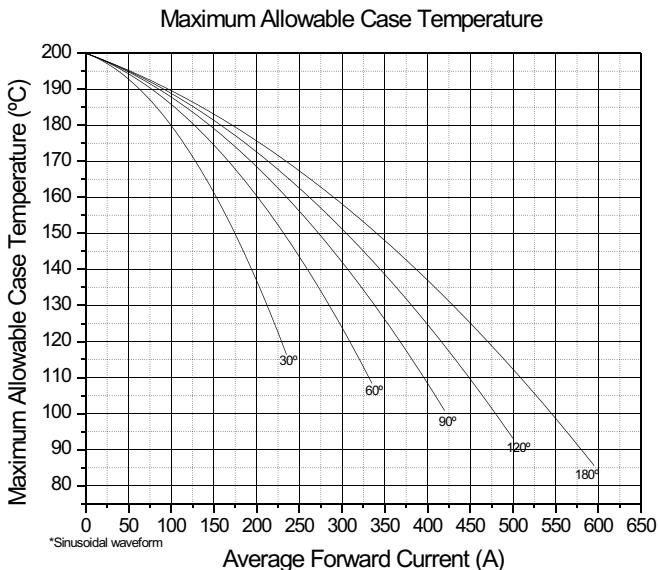


Fig. 1 - Current Ratings Characteristics

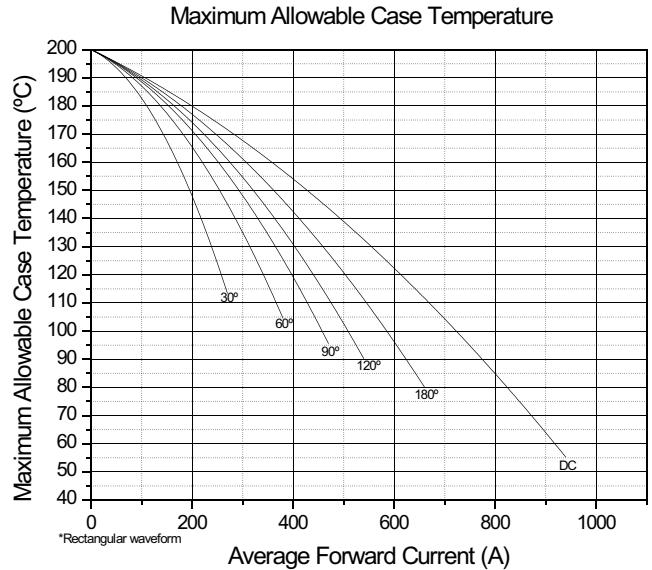
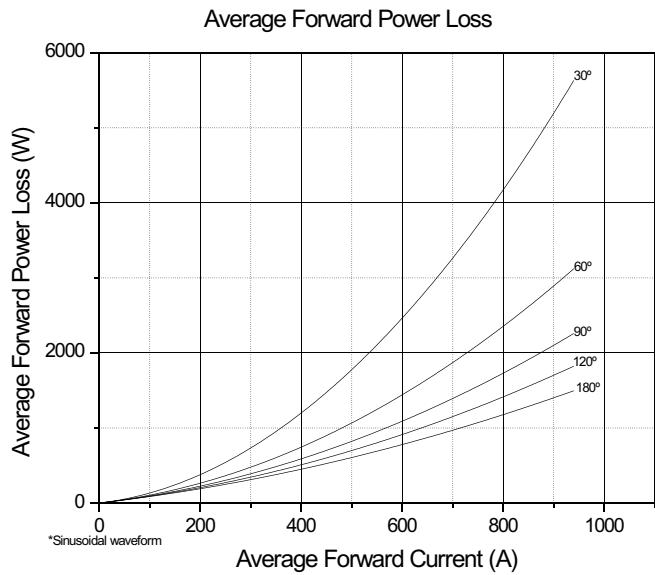


Fig. 2 - Current Ratings Characteristics



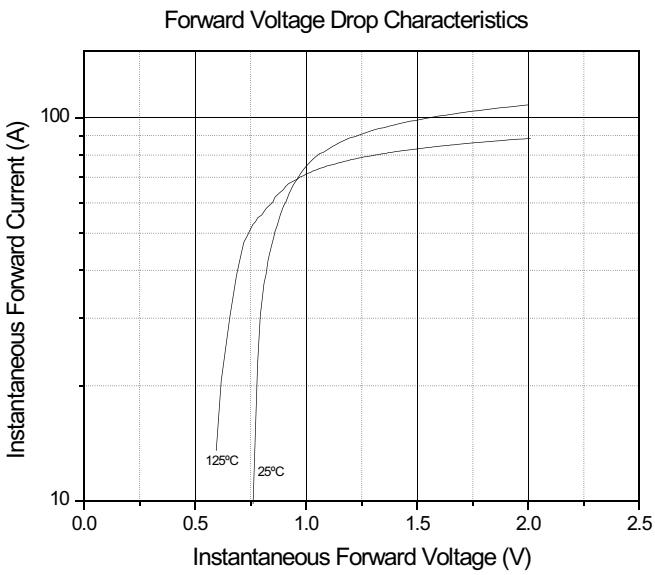
## A1A:450.XX



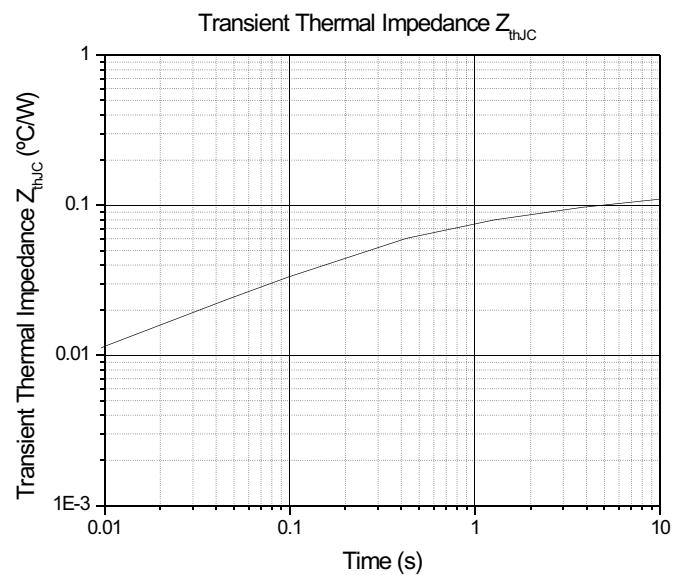
**Fig. 3 - Forward Power Loss Characteristics**



**Fig. 4 - Forward Power Loss Characteristics**



**Fig. 5 - Forward Voltage Drop Characteristics**



**Fig. 6 - Transient Thermal Impedance Characteristics**



**AEGIS**  
SEMICONDUTORES LTDA.

**A1A:450.XX**

**DO-205AB (DO-9)**

